

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| BV _{DSS} | R _{DS(ON)} MAX | I _D MAX T _A = +25°C |
|-------------------|--------------------------------|--|
| -30V | 50mΩ @ V _{GS} = -10V | -4.3A |
| | 70mΩ @ V _{GS} = -4.5V | -3.7A |

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

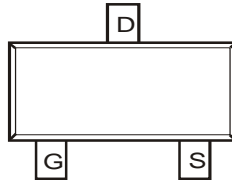
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.009 grams (Approximate)

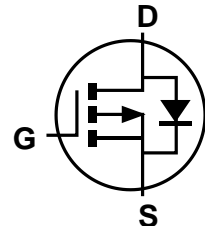
SOT23 (Standard)



Top View



Top View
Pin Configuration



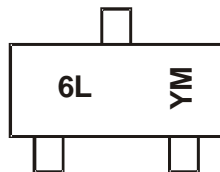
Equivalent Circuit

Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-------------|------------------|-------------------|
| DMP3056L-7 | SOT23 (Standard) | 3000/Tape & Reel |
| DMP3056L-13 | SOT23 (Standard) | 10000/Tape & Reel |

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



6L = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: 1 = 2021)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2014 | ... | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 | 2027 | 2028 | 2029 | 2030 |
|------|------|-----|------|------|------|------|------|------|------|------|------|------|
| Code | B | ... | I | J | K | L | M | N | O | P | R | S |

| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|--------------|---------------------------|-----------|----------|------|
| Drain-Source Voltage | | | V_{DSS} | -30 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 25 | V |
| Drain Current (Note 5) $V_{GS} = -10\text{V}$ | Steady State | $T_A = +25^\circ\text{C}$ | I_D | -4.3 | A |
| | | $T_A = +70^\circ\text{C}$ | | -3.4 | |
| Pulsed Drain Current (Note 6) | | | I_{DM} | -20 | A |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 5) | P_D | 1.38 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | $R_{\theta JA}$ | 91 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|---|--------------|-----|----------|------------------------|------------------|--|
| OFF CHARACTERISTICS (Note 7) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | -30 | — | — | V | $V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | — | — | -1 | μA | $V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 100 ± 800 | nA | $V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$ $V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 7) | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | -1 | — | -2.1 | V | $V_{DS} = V_{GS}, I_D = -250\mu\text{A}$ |
| Static Drain-Source On-Resistance | $R_{DS(ON)}$ | — | 35 50 | 50 70 | $\text{m}\Omega$ | $V_{GS} = -10\text{V}, I_D = -6.0\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -5.0\text{A}$ |
| Diode Forward Voltage | V_{SD} | — | — | -1.2 | V | $V_{GS} = 0\text{V}, I_S = -1.7\text{A}$ |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | |
| Input Capacitance | C_{iss} | — | 642 | — | pF | $V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$ |
| Output Capacitance | C_{oss} | — | 65 | — | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | 48 | — | pF | |
| Gate Resistance | R_G | — | 15 | — | Ω | $V_{DS} = 0\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$ |
| Total Gate Charge ($V_{GS} = -4.5\text{V}$) | Q_G | — | 5.8 | — | nC | $V_{DS} = -15\text{V}, I_D = -6\text{A}$ |
| Total Gate Charge ($V_{GS} = -10\text{V}$) | Q_G | — | 11.8 | — | nC | $V_{DS} = -15\text{V}, I_D = -6\text{A}$ |
| Gate-Source Charge | Q_{GS} | — | 2.0 | — | | |
| Gate-Drain Charge | Q_{GD} | — | 2.4 | — | | |
| Turn-On Delay Time | $t_{D(ON)}$ | — | 4.9 | — | ns | $V_{DS} = -15\text{V}, V_{GS} = -10\text{V},$ $I_D = -1\text{A}, R_G = 6.0\Omega$ |
| Rise Time | t_R | — | 4.7 | — | | |
| Turn-Off Delay Time | $t_{D(OFF)}$ | — | 35.2 | — | | |
| Fall Time | t_F | — | 18.2 | — | | |

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

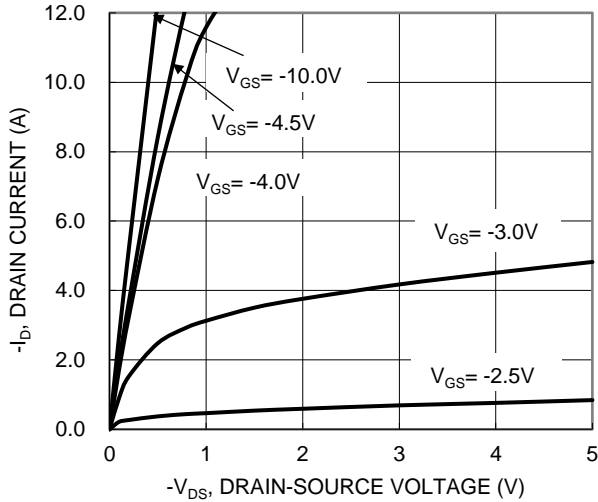


Figure 1. Typical Output Characteristic

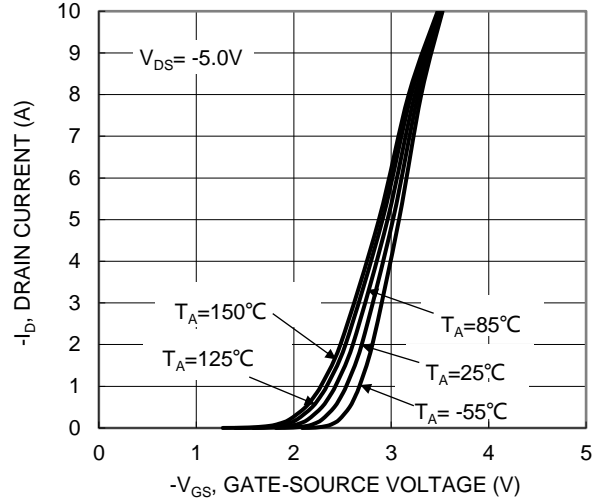


Figure 2. Typical Transfer Characteristic

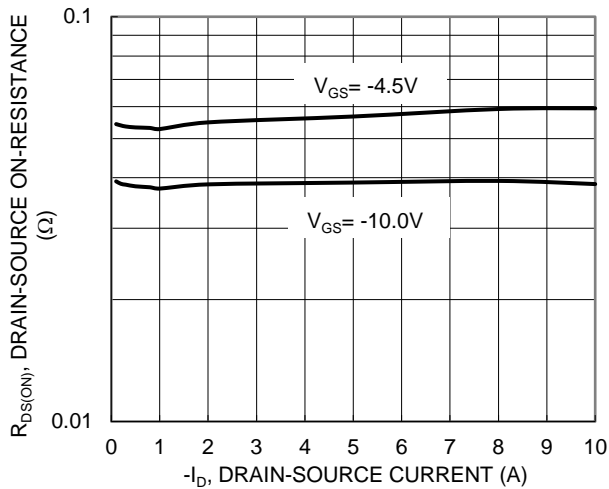


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

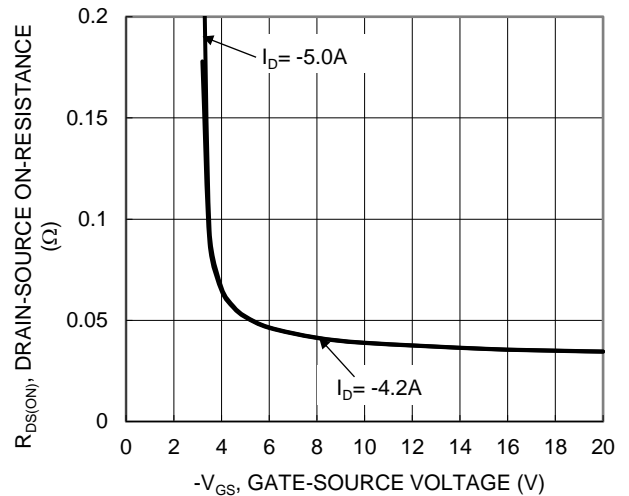


Figure 4. Typical Transfer Characteristic

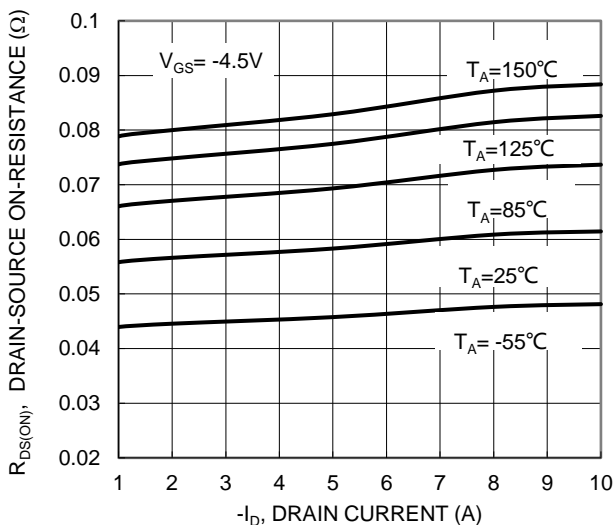


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

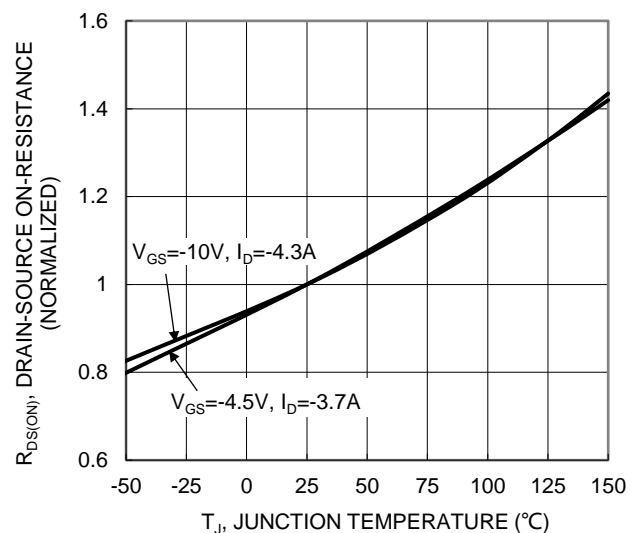


Figure 6. On-Resistance Variation with Temperature

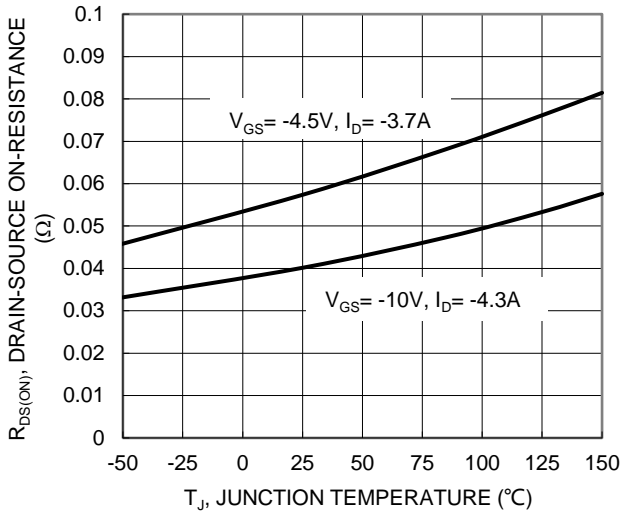


Figure 7. On-Resistance Variation with Temperature

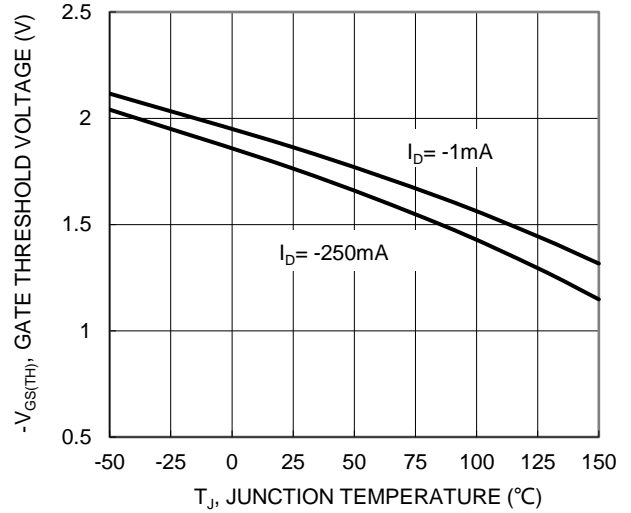


Figure 8. Gate Threshold Variation vs. Junction Temperature

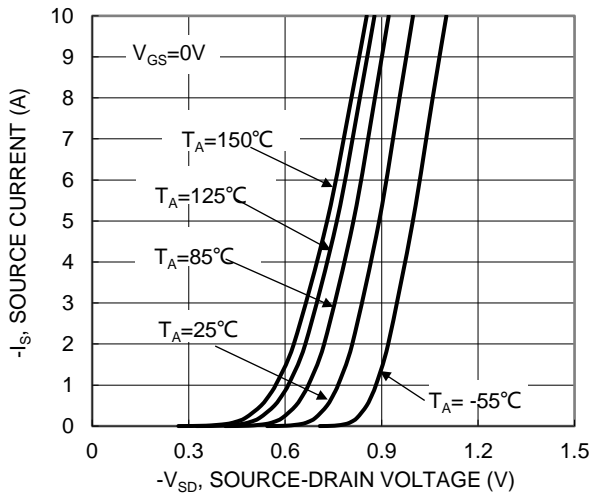


Figure 9. Diode Forward Voltage vs. Current

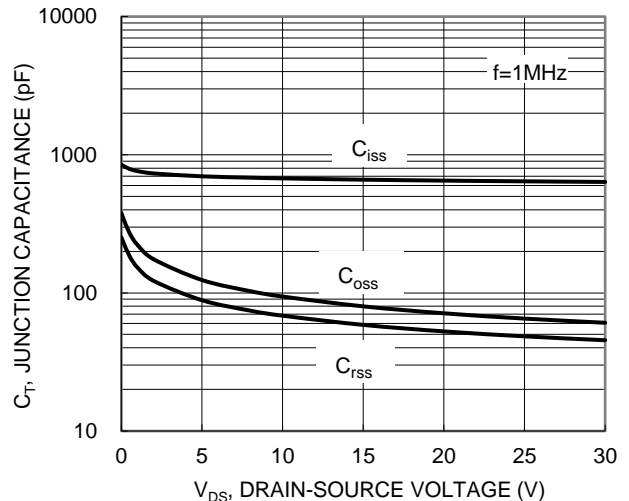


Figure 10. Typical Junction Capacitance

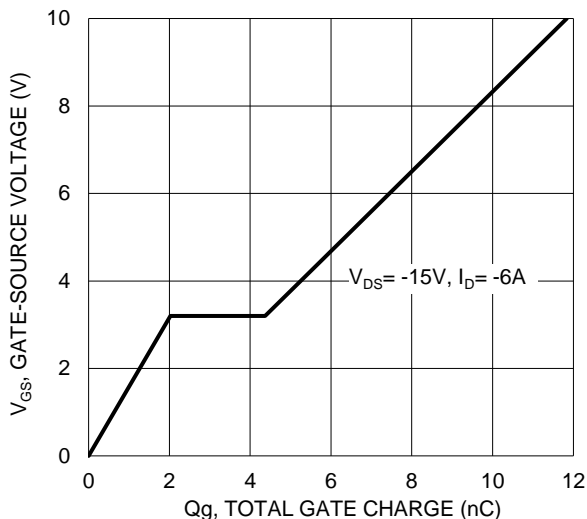


Figure 11. Gate Charge

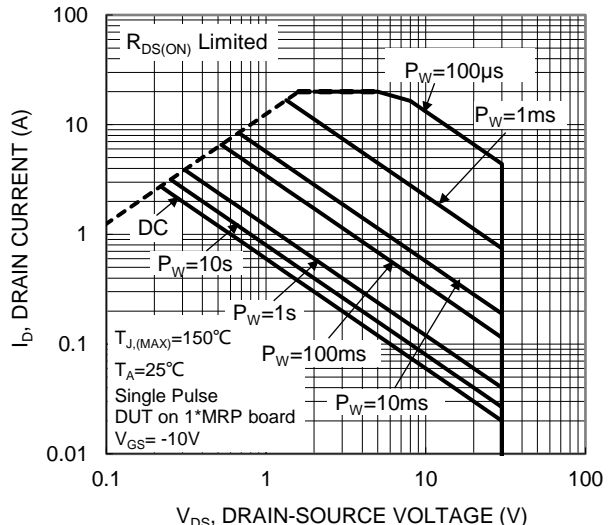


Figure 12. SOA, Safe Operation Area

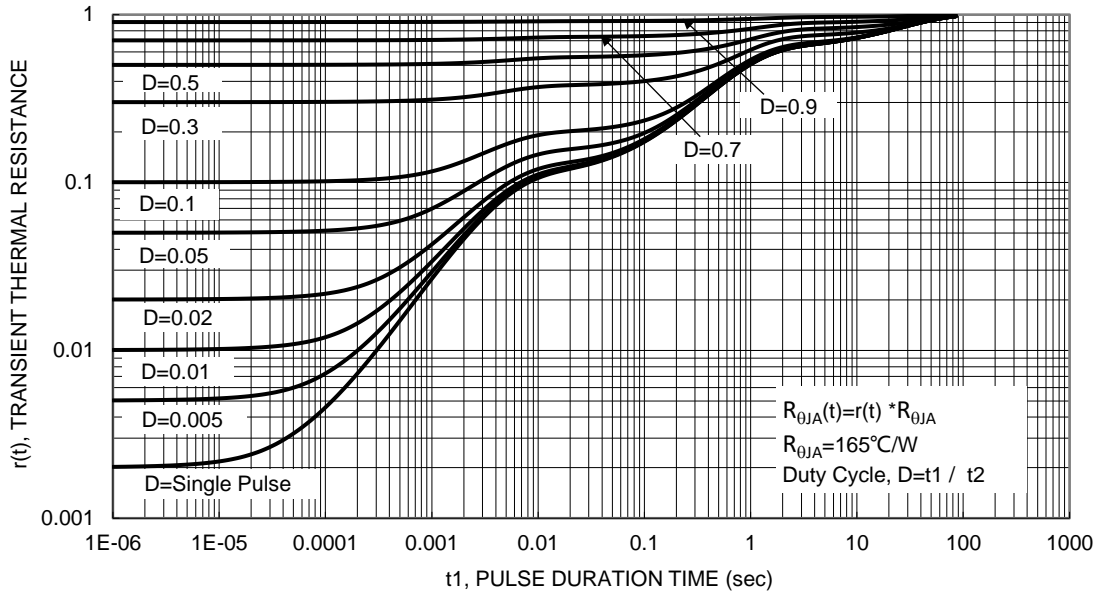
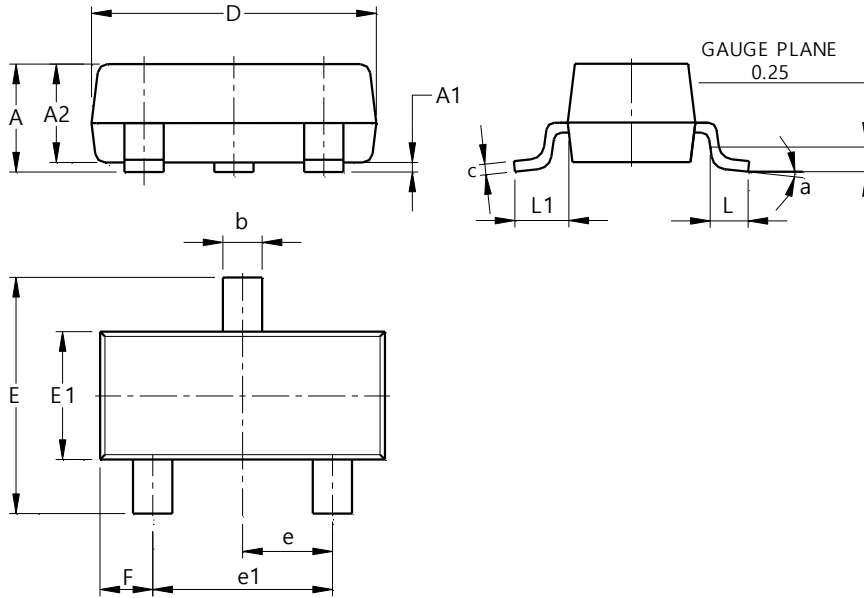


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)

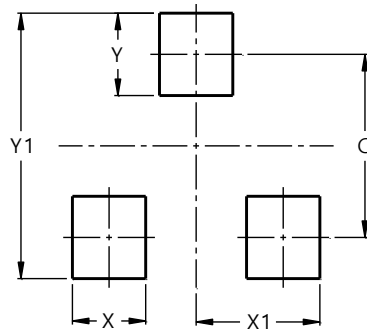


| SOT23 (Standard) | | | |
|----------------------|-------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.15 | 1.025 |
| A1 | 0.00 | 0.10 | 0.05 |
| A2 | 0.85 | 1.10 | 0.975 |
| b | 0.30 | 0.51 | 0.40 |
| c | 0.080 | 0.202 | 0.11 |
| D | 2.80 | 3.00 | 2.90 |
| E | 2.25 | 2.55 | 2.40 |
| E1 | 1.20 | 1.40 | 1.30 |
| e | 0.89 | 1.03 | 0.915 |
| e1 | 1.78 | 2.05 | 1.83 |
| F | 0.40 | 0.60 | 0.535 |
| L1 | 0.45 | 0.61 | 0.55 |
| L | 0.25 | 0.55 | 0.40 |
| a | 0° | 8° | -- |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT23 (Standard)



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 2.0 |
| X | 0.8 |
| X1 | 1.35 |
| Y | 0.9 |
| Y1 | 2.9 |

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